Integrated Device Technology, Inc.

HIGH-SPEED 1K x 8 DUAL-PORT STATIC RAM

IDT7130SA/LA
IDT7140SA/LA

FEATURES

- High-speed access
  - —Military: 25/35/55/100ns (max.)
  - —Commercial: 25/35/55/100ns (max.)
  - —Commercial: 20ns 7130 in PLCC and TQFP
- Low-power operation
  - —IDT7130/IDT7140SA
    - Active: 550mW (typ.)
    - Standby: 5mW (typ.)
  - —IDT7130/IDT7140LA
    - Active: 550mW (typ.)
    - Standby: 1mW (typ.)
- MASTER IDT7130 easily expands data bus width to 16-or-more-bits using SLAVE IDT7140
- On-chip port arbitration logic (IDT7130 Only)
- $\overline{BUSY}$ output flag on IDT7130; $\overline{BUSY}$ input on IDT7140
- Interrupt flags for port-to-port communication
- Fully asynchronous operation from either port
- Battery backup operation–2V data retention (LA only)
- TTL-compatible, single 5V ±10% power supply
- Military product compliant to MIL-STD-883, Class B
- Standard Military Drawing #5962-86875
- Industrial temperature range (–40°C to +85°C) is available, tested to military electrical specifications

DESCRIPTION

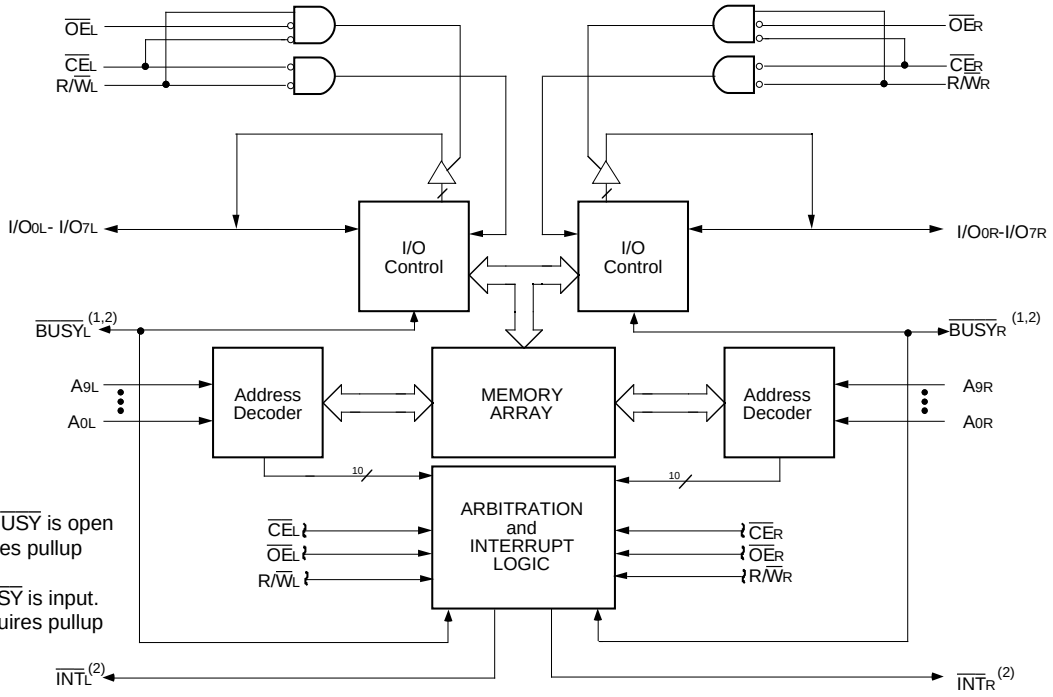
The IDT7130/IDT7140 are high-speed 1K x 8 Dual-Port Static RAMs. The IDT7130 is designed to be used as a stand-alone 8-bit Dual-Port RAM or as a "MASTER" Dual-Port RAM together with the IDT7140 "SLAVE" Dual-Port in 16-bit-or-more word width systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 16-or-more-bit memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

Both devices provide two independent ports with separate control, address, and I/O pins that permit independent asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by $\overline{CE}$, permits the on chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 550mW of power. Low-power (LA) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT7130/IDT7140 devices are packaged in 48-pin sidebraze or plastic DIPs, LCCs, or flatpacks, 52-pin PLCC, and 64-pin TQFP and STQFP. Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

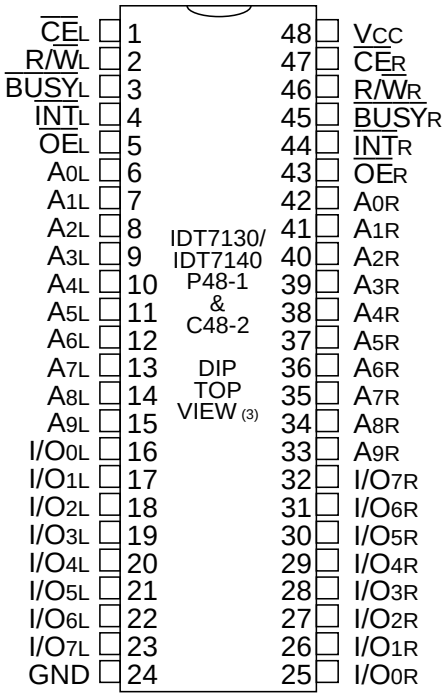
FUNCTIONAL BLOCK DIAGRAM



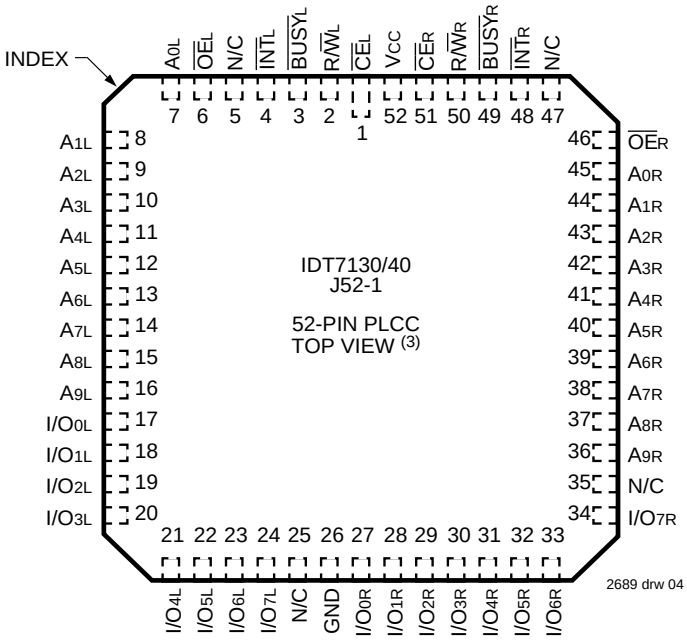
NOTES:
1. IDT7130 (MASTER): $\overline{BUSY}$ is open drain output and requires pullup resistor of 270Ω.
   IDT7140 (SLAVE): $\overline{BUSY}$ is input.
2. Open drain output: requires pullup resistor of 270Ω.

2689 drw 01

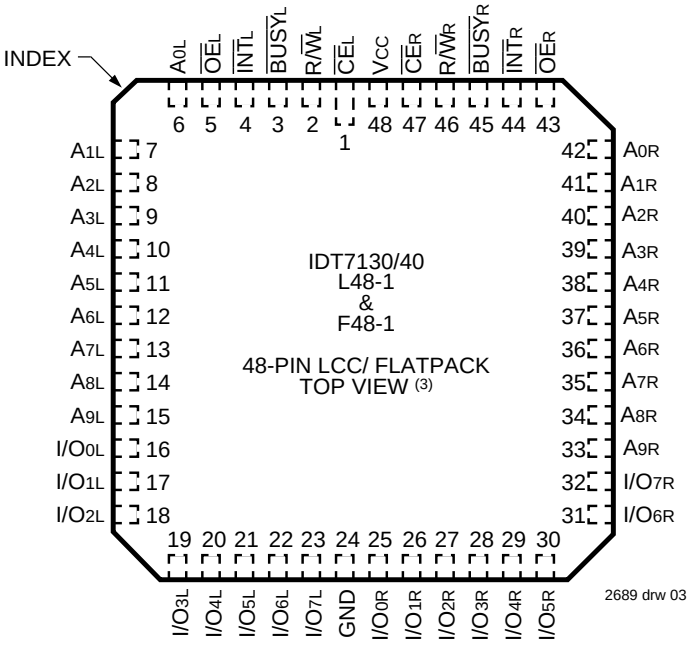
PIN CONFIGURATIONS [1,2]



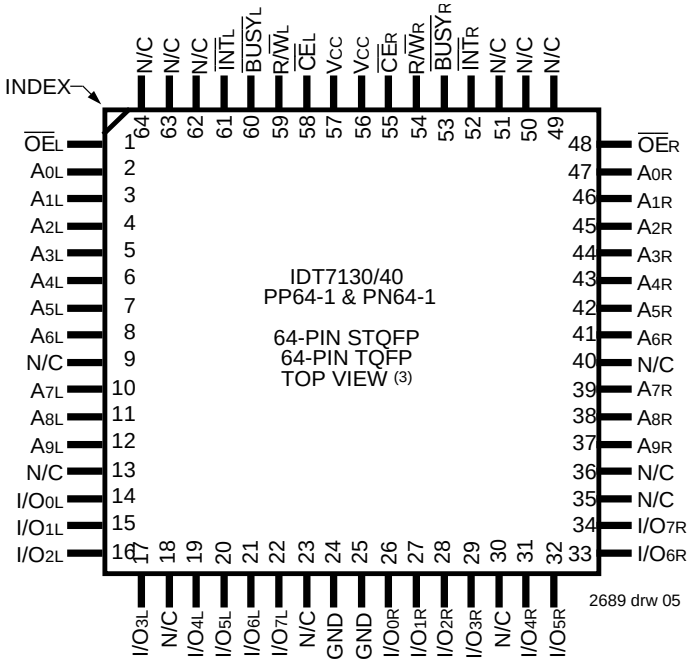
2689 drw 02



2689 drw 04



2689 drw 03



2689 drw 05

NOTES:
1. All Vcc pins must be connected to the power supply.
2. All GND pins must be connected to the ground supply.
3. This text does not indicate orientation of the actual part-marking.

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Rating	Commercial	Military	Unit
V_{TERM}(2)	Terminal Voltage with Respect to GND	–0.5 to +7.0	–0.5 to +7.0	V
T_A	Operating Temperature	0 to +70	–55 to +125	°C
T_{BIAS}	Temperature Under Bias	–55 to +125	–65 to +135	°C
T_{STG}	Storage Temperature	–55 to +125	–65 to +150	°C
I_{OUT}	DC Output Current	50	50	mA

2689 tbl 01

NOTES:
1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. VTERM must not exceed Vcc + 0.5 for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 0.5V.

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{CC}	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V_{IH}	Input High Voltage	2.2	—	6.0(2)	V
V_{IL}	Input Low Voltage	–0.5(1)	—	0.8	V

2689 tbl 02

NOTES:
1. V_{IL} (min.) ≥ -1.5V for pulse width less than 10ns.
2. V_{TERM} must not exceed Vcc + 0.5V.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Ambient Temperature	GND	Vcc
Military	–55°C to +125°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%

2689 tbl 03

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE (V_{CC} = 5.0V ± 10%)

Symbol	Parameter	Test Conditions	7130SA 7140SA Min.	7130SA 7140SA Max.	7130LA 7140LA Max.	7130LA 7140LA Max.	Unit
$\|I_{LI}\|$	Input Leakage Current(1)	V_{CC} = 5.5V, V_{IN} = 0V to V_{CC}	—	10	—	5	µA
$\|I_{LO}\|$	Output Leakage Current(1)	V_{CC} = 5.5V, $\overline{CE}$ = V_{IH}, V_{OUT} = 0V to V_{CC}	—	10	—	5	µA
V_{OL}	Output Low Voltage (I/O0-I/O7)	I_{OL} = 4mA	—	0.4	—	0.4	V
V_{OL}	Open Drain Output Low Voltage ($\overline{BUSY}$, $\overline{INT}$)	I_{OL} = 16mA	—	0.5	—	0.5	V
V_{OH}	Output High Voltage	I_{OH} = -4mA	2.4	—	2.4	—	V

2689 tbl 04

NOTE:
1. At Vcc ≤ 2.0V leakages are undefined.

CAPACITANCE(1)

(T_A = +25°C, f = 1.0MHz) TQFP ONLY(3)

Symbol	Parameter	Conditions(2)	Max.	Unit
C_{IN}	Input Capacitance	V_{IN} = 3dV	9	pF
C_{OUT}	Output Capacitance	V_{IN} = 3dV	10	pF

2689 tbl 05

NOTES:
1. This parameter is determined by device characterization but is not production tested.
2. 3dv references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.
3. 11pF max. for other packages.

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE[1,6] (V_{CC} = 5.0V ± 10%)

Symbol	Parameter	Test Conditions	Version	7130X20[2] Typ.	7130X20[2] Max.	7130X25[3] 7140X25[3] Typ.	7130X25[3] 7140X25[3] Max.	7130X35 7140X35 Typ.	7130X35 7140X35 Max.	7130X55 7140X55 Typ.	7130X55 7140X55 Max.	7130X100 7140X100 Typ.	7130X100 7140X100 Max.	Unit
I_{CC}	Dynamic Operating Current (Both Ports Active)	$\overline{CE}_L$ and $\overline{CE}_R$ = V_{IL}, Outputs open, f = f_{MAX}[4]	MIL. SA	—	—	110	280	110	230	110	190	110	190	mA
			MIL. LA	—	—	110	220	110	170	110	140	110	140	
			COM'L. SA	110	250	110	220	110	165	110	155	110	155	
			COM'L. LA	110	200	110	170	110	120	110	110	110	110	
I_{SB1}	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}_L$ and $\overline{CE}_R$ = V_{IH}, f = f_{MAX}[4]	MIL. SA	—	—	30	80	25	80	20	65	20	65	mA
			MIL. LA	—	—	30	60	25	60	20	45	20	45	
			COM'L. SA	30	65	30	65	25	65	20	65	20	55	
			COM'L. LA	30	45	30	45	25	45	20	35	20	35	
I_{SB2}	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}_{"A"}$ = V_{IL} and $\overline{CE}_{"B"}$ = V_{IH}[7] Active Port Outputs Open, f = f_{MAX}[4]	MIL. SA	—	—	65	160	50	150	40	125	40	125	mA
			MIL. LA	—	—	65	125	50	115	40	90	40	90	
			COM'L. SA	65	165	65	150	50	125	40	110	40	110	
			COM'L. LA	65	125	65	115	50	90	40	75	40	75	
I_{SB3}	Full Standby Current (Both Ports - All CMOS Level Inputs	$\overline{CE}_L$ and $\overline{CE}_R \geq V_{CC}$ -0.2V, $V_{IN} \geq V_{CC}$ -0.2V or $V_{IN} \leq$ 0.2V, f = 0[5]	MIL. SA	—	—	1.0	30	1.0	30	1.0	30	1.0	30	mA
			MIL. LA	—	—	0.2	10	0.2	10	0.2	10	0.2	10	
			COM'L. SA	1.0	15	1.0	15	1.0	15	1.0	15	1.0	15	
			COM'L. LA	0.2	5	0.2	5	0.2	4	0.2	4	0.2	4	
I_{SB4}	Full Standby Current (One Port - All CMOS Level Inputs)	$\overline{CE}_{"A"} \leq$ 0.2V and $\overline{CE}_{"B"} \geq V_{CC}$ -0.2V[7] $V_{IN} \geq V_{CC}$ -0.2V or $V_{IN} \leq$ 0.2V, Active Port Outputs Open, f = f_{MAX}[4]	MIL. SA	—	—	60	155	45	145	40	110	40	110	mA
			MIL. LA	—	—	60	115	45	105	40	85	40	80	
			COM'L. SA	60	155	60	145	45	110	40	100	40	95	
			COM'L. LA	60	115	60	105	45	85	40	70	40	70	

NOTES:

2689 tbl 06

1. 'X' in part numbers indicates power rating (SA or LA).
2. Com'l Only, 0°C to +70°C temperature range. PLCC and TQFP packages.
3. Not available in DIP packages.
4. At f = f_{Max}, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/t_{RC}, and using "AC TEST CONDITIONS" of input levels of GND to 3V.
5. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
6. Vcc = 5V, T_A=+25°C for Typ and is not production tested. $V_{CC\,DC}$ = 100 mA (Typ.)
7. Port "A" may be either left or right port. Port "B" is opposite from port "A".

DATA RETENTION CHARACTERISTICS (LA Version Only)

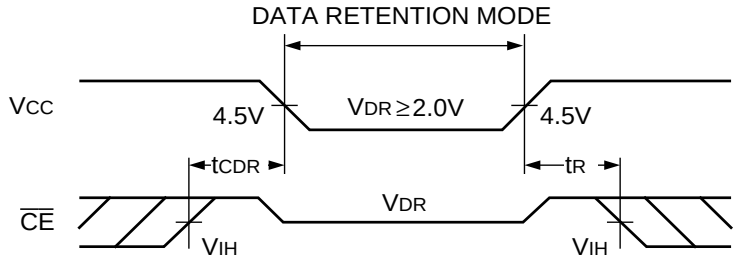
Symbol	Parameter	Test Conditions		IDT7130LA/IDT7140LA Min.	Typ.[1]	Max.	Unit
V_{DR}	V_{CC} for Data Retention	V_{CC} = 2.0V, $\overline{CE} \geq V_{CC}$ -0.2V $V_{IN} \geq V_{CC}$ -0.2V or $V_{IN} \leq$ 0.2V		2.0	—	—	V
I_{CCDR}	Data Retention Current		Mil.	—	100	4000	µA
			Com'l.	—	100	1500	µA
t_{CDR}[3]	Chip Deselect to Data Retention Time			0	—	—	ns
t_R[3]	Operation Recovery Time			t_{RC}[2]	—	—	ns

2689 tbl 07

NOTES:

1. V_{CC} = 2V, T_A = +25°C, and is not production tested.
2. t_{RC} = Read Cycle Time
3. This parameter is guaranteed but not production tested.

DATA RETENTION WAVEFORM



2692 drw 06

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

2689 tbl 08

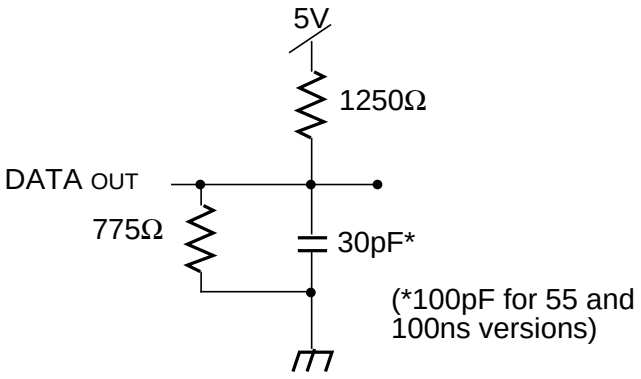


Figure 1. Output Test Load

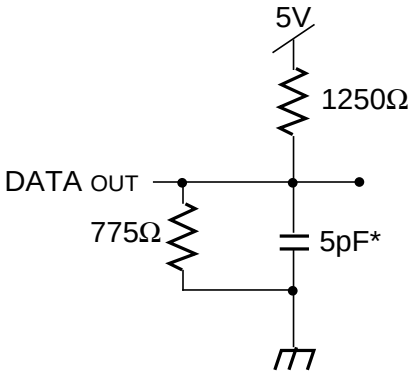
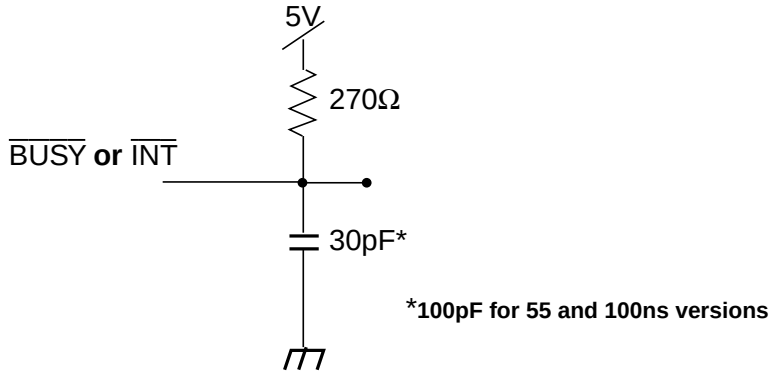


Figure 2. Output Test Load
(for tHZ, tLZ, tWZ, and tOW)
*** including scope and jig**



2689 drw 07

Figure 3. BUSY and INT
AC Output Test Load

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE(3)

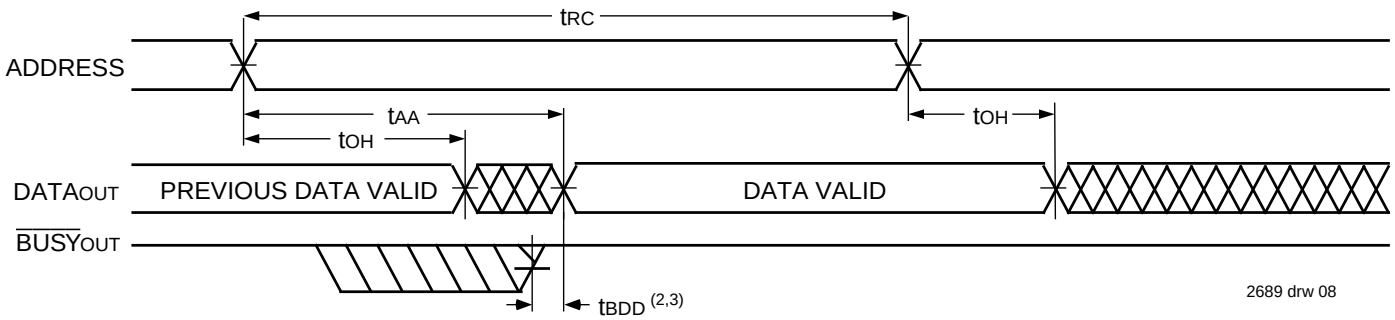
Symbol	Parameter	7130X20(2) Min.	7130X20(2) Max.	7130X25(5) 7140X25(5) Min.	7130X25(5) 7140X25(5) Max.	7130X35 7140X35 Min.	7130X35 7140X35 Max.	7130X55 7140X55 Min.	7130X55 7140X55 Max.	7130X100 7140X100 Min.	7130X100 7140X100 Max.	Unit
Read Cycle												
t_{RC}	Read Cycle Time	20	—	25	—	35	—	55	—	100	—	ns
t_{AA}	Address Access Time	—	20	—	25	—	35	—	55	—	100	ns
t_{ACE}	Chip Enable Access Time	—	20	—	25	—	35	—	55	—	100	ns
t_{AOE}	Output Enable Access Time		11	—	12	—	20	—	25	—	40	ns
t_{OH}	Output Hold From Address Change	3	—	3	—	3	—	3	—	10	—	ns
t_{LZ}	Output Low-Z Time(1,4)	0	—	0	—	0	—	5	—	5	—	ns
t_{HZ}	Output High-Z Time(1,4)	—	10	—	10	—	15	—	25	—	40	ns
t_{PU}	Chip Enable to Power Up Time(4)	0	—	0	—	0	—	0	—	0	—	ns
t_{PD}	Chip Disable to Power Down Time(4)	—	20	—	25	—	35	—	50	—	50	ns

NOTES:

2689 tbl 09

1. Transition is measured ±500mV from Low or High-impedance voltage Output Test Load (Figure 2).
2. Com'l Only, 0°C to +70°C temperature range. PLCC and TQFP package.
3. "X" in part numbers indicates power rating (SA or LA).
4. This parameter is guaranteed by device characterization, but is not production tested.
5. Not available in DIP packages.

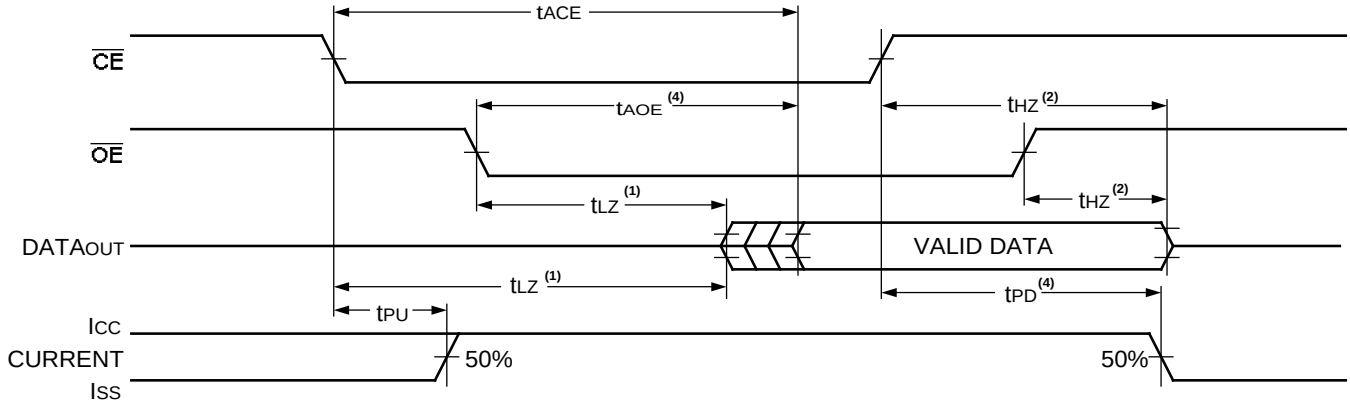
TIMING WAVEFORM OF READ CYCLE NO. 1, EITHER SIDE(1)



NOTES:

1. R/$\overline{W}$ = V_{IH}, $\overline{CE}$ = V_{IL}, and is $\overline{OE}$ = V_{IL}. Address is valid prior to the coincidental with $\overline{CE}$ transition Low.
2. t_{BDD} delay is required only in the case where the opposite port is completing a write operation to the same the address location. For simultaneous read operations, $\overline{BUSY}$ has no relationship to valid output data.
3. Start of valid data depends on which timing becomes effective last t_{AOE}, t_{ACE}, t_{AA}, and t_{BDD}.

TIMING WAVEFORM OF READ CYCLE NO. 2, EITHER SIDE(3)



2689 drw 09

NOTES:
1. Timing depends on which signal is asserted last, $\overline{OE}$ or $\overline{CE}$.
2. Timing depends on which signal is deasserted first, $\overline{OE}$ or $\overline{CE}$.
3. R/$\overline{W}$ = V_{IH} and the address is valid prior to or coincidental with $\overline{CE}$ transition Low.
4. Start of valid data depends on which timing becomes effective last t_{AOE}, t_{ACE}, t_{AA}, and t_{BDD}.

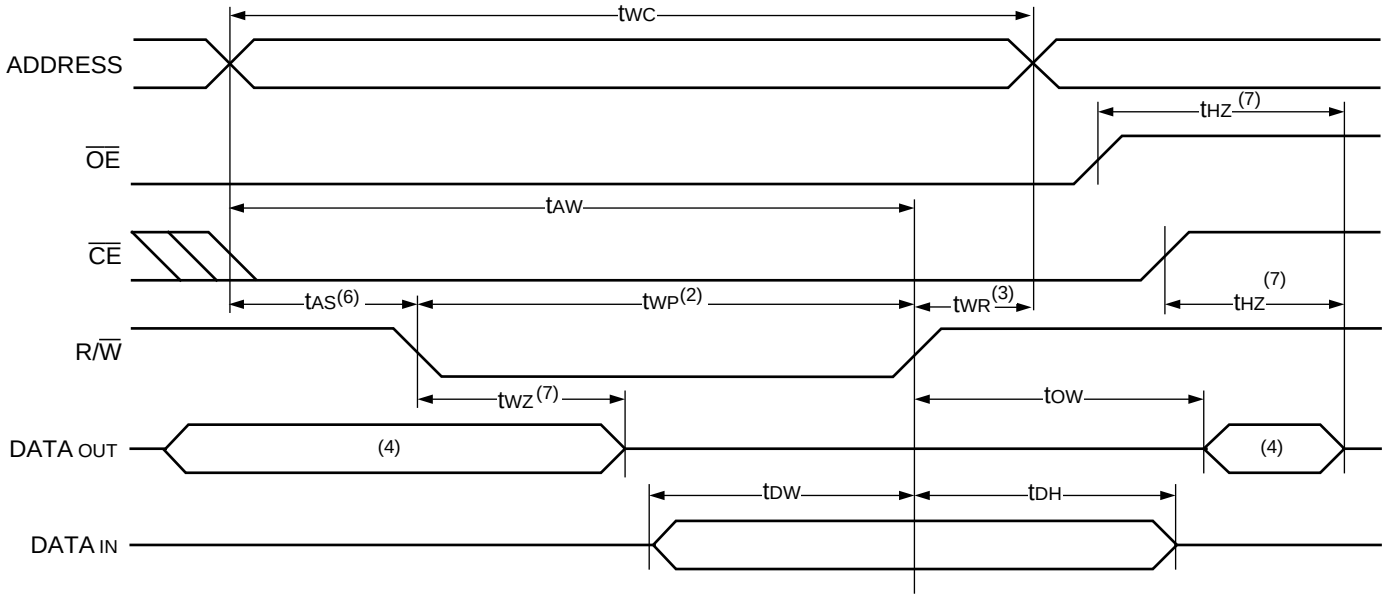
AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE(5)

Symbol	Parameter	7130X20(2) Min.	7130X20(2) Max.	7130X25(6) 7140X25(6) Min.	7130X25(6) 7140X25(6) Max.	7130X35 7140X35 Min.	7130X35 7140X35 Max.	7130X55 7140X55 Min.	7130X55 7140X55 Max.	7130X100 7140X100 Min.	7130X100 7140X100 Max.	Unit
Write Cycle												
t_{WC}	Write Cycle Time(3)	20	—	25	—	35	—	55	—	100	—	ns
t_{EW}	Chip Enable to End-of-Write	15	—	20	—	30	—	40	—	90	—	ns
t_{AW}	Address Valid to End-of-Write	15	—	20	—	30	—	40	—	90	—	ns
t_{AS}	Address Set-up Time	0	—	0	—	0	—	0	—	0	—	ns
t_{WP}	Write Pulse Width(4)	15	—	15	—	25	—	30	—	55	—	ns
t_{WR}	Write Recovery Time	0	—	0	—	0	—	0	—	0	—	ns
t_{DW}	Data Valid to End-of-Write	10	—	12	—	15	—	20	—	40	—	ns
t_{HZ}	Output High-Z Time(1)	—	10	—	10	—	15	—	25	—	40	ns
t_{DH}	Data Hold Time	0	—	0	—	0	—	0	—	0	—	ns
t_{WZ}	Write Enabled to Output in High-Z(1)	—	10	—	10	—	15	—	25	—	40	ns
t_{OW}	Output Active From End-of-Write(1)	0	—	0	—	0	—	0	—	0	—	ns

2689 tbl 10

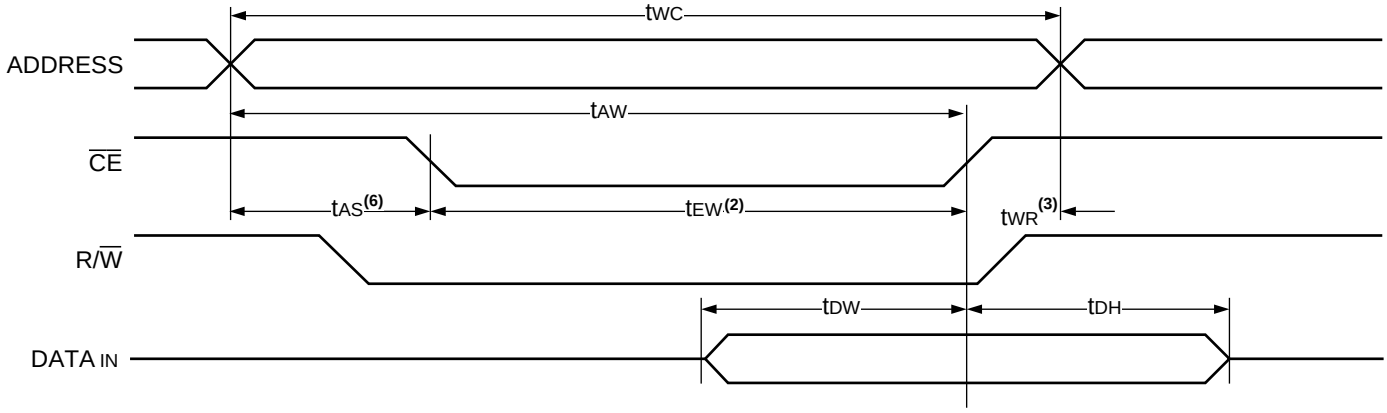
NOTES:
1. Transition is measured ±500mV from Low or High-impedance voltage with Output Test Load (Figure 2). This parameter is guaranteed by device characterization but is not production tested.
2. 0°C to +70°C temperature range only, PLCC and TQFP packages.
3. For MASTER/SLAVE combination, t_{WC} = t_{BAA} + t_{WP}, since R/$\overline{W}$ = V_{IL} must occur after t_{BAA}.
4. If $\overline{OE}$ is low during a R/$\overline{W}$ controlled write cycle, the write pulse width must be the larger of t_{WP} or (t_{WZ} + t_{DW}) to allow the I/O drivers to turn off data to be placed on the bus for the required t_{DW}. If $\overline{OE}$ is High during a R/$\overline{W}$ controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified t_{WP}.
5. "X" in part numbers indicates power rating (SA or LA).
6. Not available in DIP packages.

TIMING WAVEFORM OF WRITE CYCLE NO. 1, (R/$\overline{W}$ CONTROLLED TIMING)(1,5,8)



2689 drw 10

TIMING WAVEFORM OF WRITE CYCLE NO. 2, ($\overline{CE}$ CONTROLLED TIMING)(1,5)



2689 drw 11

NOTES:
1. R/$\overline{W}$ or $\overline{CE}$ must be High during all address transitions.
2. A write occurs during the overlap (t_{EW} or t_{WP}) of $\overline{CE}$ = V_{IL} and R/$\overline{W}$ = V_{IL}.
3. t_{WR} is measured from the earlier of $\overline{CE}$ or R/$\overline{W}$ going High to the end of the write cycle.
4. During this period, the I/O pins are in the output state and input signals must not be applied.
5. If the $\overline{CE}$ Low transition occurs simultaneously with or after the R/$\overline{W}$ Low transition, the outputs remain in the High-impedance state.
6. Timing depends on which enable signal ($\overline{CE}$ or R/$\overline{W}$) is asserted last.
7. This parameter is determined be device characterization, but is not production tested. Transition is measured +/- 500mV from steady state with the Output Test Load (Figure 2).
8. If $\overline{OE}$ is low during a R/$\overline{W}$ controlled write cycle, the write pulse width must be the larger of t_{WP} or (t_{WZ} + t_{DW}) to allow the I/O drivers to turn off and data to be placed on the bus for the required t_{DW}. If $\overline{OE}$ is High during a R/$\overline{W}$ controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified t_{WP}.

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE(7)

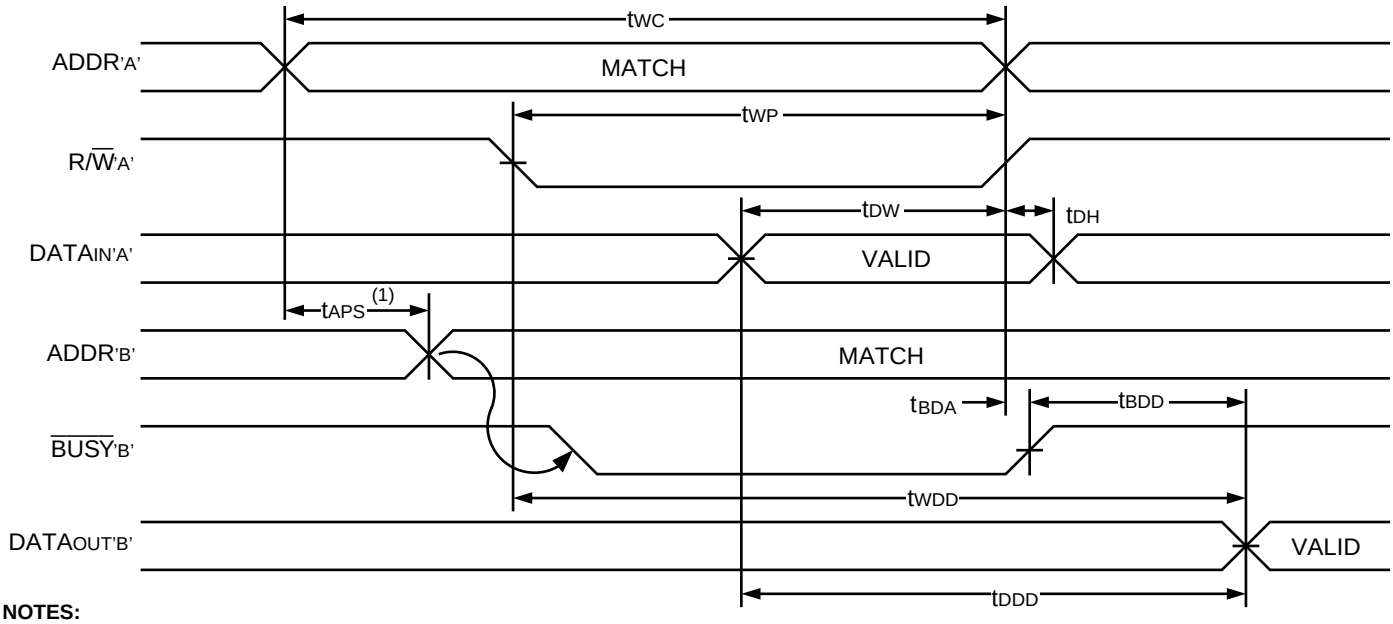
Symbol	Parameter	7130X20(1) Min.	7130X20(1) Max.	7130X25(9) 7140X25(9) Min.	7130X25(9) 7140X25(9) Max.	7130X35 7140X35 Min.	7130X35 7140X35 Max.	7130X55 7140X55 Min.	7130X55 7140X55 Max.	7130X100 7140X100 Min.	7130X100 7140X100 Max.	Unit
Busy Timing (For Master IDT7130 Only)												
t_{BAA}	$\overline{BUSY}$ Access Time from Address	—	20	—	20	—	20	—	30	—	50	ns
t_{BDA}	$\overline{BUSY}$ Disable Time from Address	—	20	—	20	—	20	—	30	—	50	ns
t_{BAC}	$\overline{BUSY}$ Access Time from Chip Enable	—	20	—	20	—	20	—	30	—	50	ns
t_{BDC}	$\overline{BUSY}$ Disable Time from Chip Enable	—	20	—	20	—	20	—	30	—	50	ns
t_{WH}	Write Hold After $\overline{BUSY}$(6)	12	—	15	—	20	—	20	—	20	—	ns
t_{WDD}	Write Pulse to Data Delay(2)	—	40	—	50	—	60	—	80	—	120	ns
t_{DDD}	Write Data Valid to Read Data Delay(2)	—	30	—	35	—	35	—	55	—	100	ns
t_{APS}	Arbitration Priority Set-up Time(3)	5	—	5	—	5	—	5	—	5	—	ns
t_{BDD}	$\overline{BUSY}$ Disable to Valid Data(4)	—	25	—	35	—	35	—	50	—	65	ns
Busy Timing (For Slave IDT7140 Only)												
t_{WB}	Write to $\overline{BUSY}$ Input(5)	0	—	0	—	0	—	0	—	0	—	ns
t_{WH}	Write Hold After $\overline{BUSY}$(6)	12	—	15	—	20	—	20	—	20	—	ns
t_{WDD}	Write Pulse to Data Delay(2)	—	40	—	50	—	60	—	80	—	120	ns
t_{DDD}	Write Data Valid to Read Data Delay(2)	—	30	—	35	—	35	—	55	—	100	ns

NOTES:

2689 tbl 11

1. Com'l Only, 0°C to +70°C temperature range. PLCC and TQFP packages only.
2. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port-to-Port Read and $\overline{BUSY}$."
3. To ensure that the earlier of the two ports wins.
4. t_{BDD} is a calculated parameter and is the greater of 0, $t_{WDD} - t_{WP}$ (actual), or $t_{DDD} - t_{DW}$ (actual).
5. To ensure that a write cycle is inhibited on port 'B' during contention on port 'A'.
6. To ensure that a write cycle is completed on port 'B' after contention on port 'A'.
7. "X" in part numbers indicates power rating (SA or LA).
8. Not available in DIP packages.

TIMING WAVEFORM OF WRITE WITH PORT-TO-PORT READ AND $\overline{BUSY}$ (2,3,4)



NOTES:

1. To ensure that the earlier of the two ports wins. t_{BDD} is ignored for slave (IDT7140).
2. $\overline{CE}_L = \overline{CE}_R = V_{IL}$.
3. OE = V_{IL} for the reading port.
4. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

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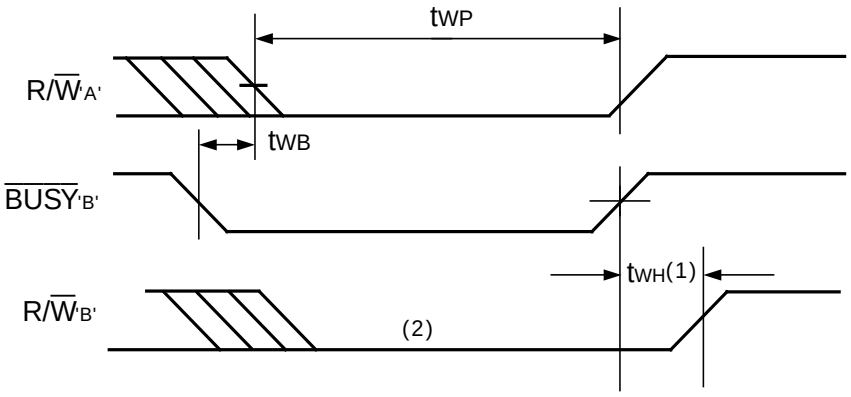
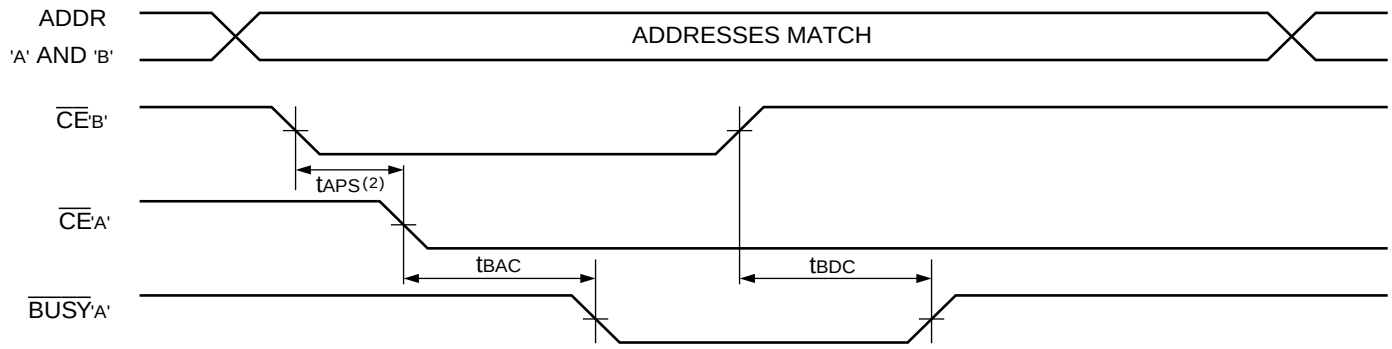
TIMING WAVEFORM OF WRITE WITH $\overline{BUSY}$ (3)



2689 drw 13

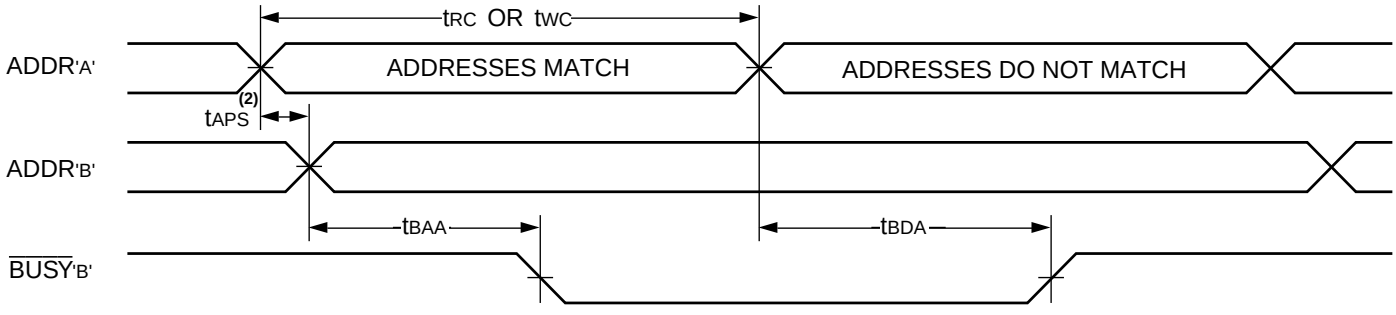
NOTES:
1. t_{WH} must be met for both BUSY Input (IDT7140, slave) or Output (IDT7130 master).
2. BUSY is asserted on port 'B' blocking R/W'B', until BUSY'B' goes High.
3. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

TIMING WAVEFORM OF BUSY ARBITRATION CONTROLLED BY $\overline{CE}$ TIMING (1)



2689 drw 14

TIMING WAVEFORM OF BUSY ARBITRATION CONTROLLED BY ADDRESS MATCH TIMING (1)



2689 drw 15

NOTES:
1. All timing is the same for left and right ports. Port “A” may be either left or right port. Port “B” is the opposite from port “A”.
2. If t_{APS} is not satisified, the $\overline{BUSY}$ will be asserted on one side or the other, but there is no guarantee on which side $\overline{BUSY}$ will be asserted (7130 only).

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE[2]

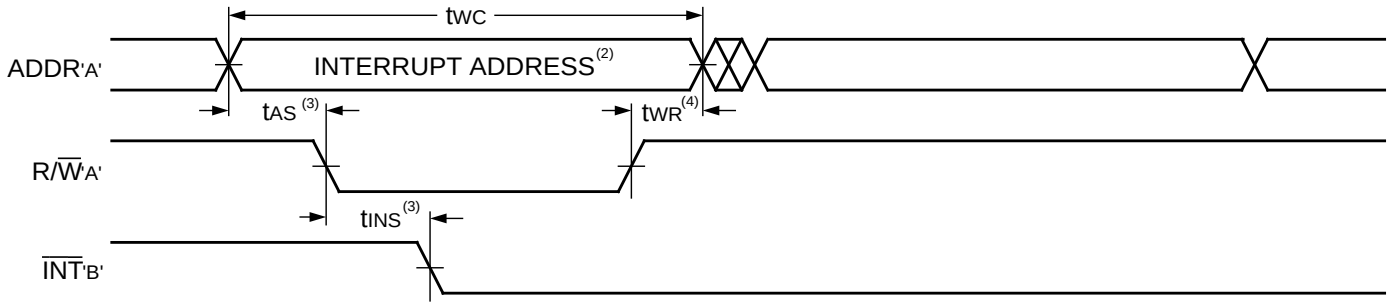
Symbol	Parameter	7130X20[1] Min.	7130X20[1] Max.	7130X25[3] 7140X25[3] Min.	7130X25[3] 7140X25[3] Max.	7130X35 7140X35 Min.	7130X35 7140X35 Max.	7130X55 7140X55 Min.	7130X55 7140X55 Max.	7130X100 7140X100 Min.	7130X100 7140X100 Max.	Unit
Interrupt Timing												
t_{AS}	Address Set-up Time	0	—	0	—	0	—	0	—	0	—	ns
t_{WR}	Write Recovery Time	0	—	0	—	0	—	0	—	0	—	ns
t_{INS}	Interrupt Set Time	—	20	—	25	—	25	—	45	—	60	ns
t_{INR}	Interrupt Reset Time	—	20	—	25	—	25	—	45	—	60	ns

2689 tbl 12

NOTES:
1. 0°C to +70°C temperature range only, PLCC and TQFP packages.
2. "X" in part numbers indicates power rating (SA or LA).
3. Not available in DIP packages .

TIMING WAVEFORM OF INTERRUPT MODE

$\overline{INT}$ SET:



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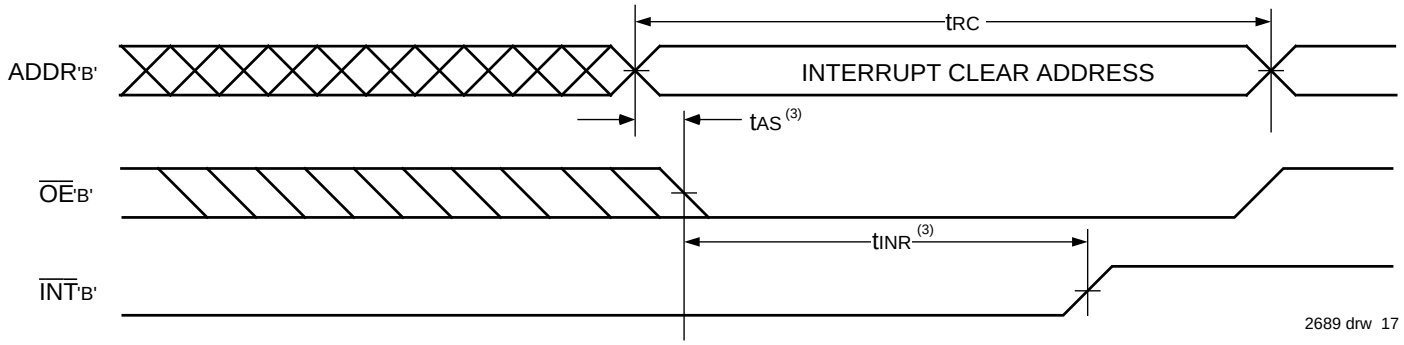
$\overline{INT}$ CLEAR:



2689 drw 17

NOTES:.
1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
2. See Interrupt Truth Table.
3. Timing depends on which enable signal ($\overline{CE}$ or R/$\overline{W}$) is asserted last.
4. Timing depends on which enable signal ($\overline{CE}$ or R/$\overline{W}$) is de-asserted first.

TRUTH TABLES

TABLE I — NON-CONTENTION READ/WRITE CONTROL(4)

Left or Right Port(1)				
R/$\overline{W}$	$\overline{CE}$	$\overline{OE}$	D_{0-7}	Function
X	H	X	Z	Port Disabled and in Power-Down Mode, I_{SB2} or I_{SB4}
X	H	X	Z	$\overline{CE}_R = \overline{CE}_L = V_{IH}$, Power-Down Mode, I_{SB1} or I_{SB3}
L	L	X	$DATA_{IN}$	Data on Port Written Into Memory(2)
H	L	L	$DATA_{OUT}$	Data in Memory Output on Port(3)
H	L	H	Z	High Impedance Outputs

NOTES: 2689 tbl 13

1. $A_{0L} – A_{10L} \neq A_{0R} – A_{10R}$.
2. If $\overline{BUSY}$ = L, data is not written.
3. If $\overline{BUSY}$ = L, data may not be valid, see t_{WDD} and t_{DDD} timing.
4. 'H' = V_{IH}, 'L' = V_{IL}, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

TABLE II — INTERRUPT FLAG(1,4)

Left Port					Right Port					
R/$\overline{W}_L$	$\overline{CE}_L$	$\overline{OE}_L$	$A_{9L} – A_{0L}$	$\overline{INT}_L$	R/$\overline{W}_R$	$\overline{CE}_R$	$\overline{OE}_R$	$A_{9L} – A_{0R}$	$\overline{INT}_R$	Function
L	L	X	3FF	X	X	X	X	X	L(2)	Set Right $\overline{INT}_R$ Flag
X	X	X	X	X	X	L	L	3FF	H(3)	Reset Right $\overline{INT}_R$ Flag
X	X	X	X	L(3)	L	L	X	3FE	X	Set Left $\overline{INT}_L$ Flag
X	L	L	3FE	H(2)	X	X	X	X	X	Reset Left $\overline{INT}_L$ Flag

NOTES: 2689 tbl 14

1. Assumes $\overline{BUSY}_L = \overline{BUSY}_R = V_{IH}$
2. If $\overline{BUSY}_L = V_{IL}$, then No Change.
3. If $\overline{BUSY}_R = V_{IL}$, then No Change.
4. 'H' = HIGH,' L' = LOW,' X' = DON'T CARE

TABLE III — ADDRESS BUSY ARBITRATION

Inputs			Outputs		
$\overline{CE}_L$	$\overline{CE}_R$	A_{0L}-A_{9L} A_{0R}-A_{9R}	$\overline{BUSY}_L$(1)	$\overline{BUSY}_R$(1)	Function
X	X	NO MATCH	H	H	Normal
H	X	MATCH	H	H	Normal
X	H	MATCH	H	H	Normal
L	L	MATCH	(2)	(2)	Write Inhibit(3)

NOTES: 2689 tbl 15

1. Pins $\overline{BUSY}_L$ and $\overline{BUSY}_R$ are both outputs for IDT7130 (master). Both are inputs for IDT7140 (slave). $\overline{BUSY}_X$ outputs on the IDT7130 are open drain, not push-pull outputs. On slaves the $\overline{BUSY}_X$ input internally inhibits writes.
2. 'L' if the inputs to the opposite port were stable prior to the address and enable inputs of this port. 'H' if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either $\overline{BUSY}_L$ or $\overline{BUSY}_R$ = Low will result. $\overline{BUSY}_L$ and $\overline{BUSY}_R$ outputs can not be low simultaneously.
3. Writes to the left port are internally ignored when $\overline{BUSY}_L$ outputs are driving Low regardless of actual logic level on the pin. Writes to the right port are internally ignored when $\overline{BUSY}_R$ outputs are driving Low regardless of actual logic level on the pin.

FUNCTIONAL DESCRIPTION

The IDT7130/IDT7140 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7130/IDT7140 has an automatic power down feature controlled by $\overline{CE}$. The $\overline{CE}$ controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{CE}$ = V_{IH}). When a port is enabled, access to the entire memory array is permitted.

INTERRUPTS

If the user chooses to use the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ($\overline{INT}_L$) is asserted when the right port writes to memory location 3FE (HEX), where a write is defined as the $\overline{CE}$ = R/$\overline{W}$ = V_{IL} per the Truth Table. The left port clears the interrupt by access address location 3FE access when $\overline{CE}_R$ = $\overline{OE}_R$ = V_{IL}, R/$\overline{W}$ is a "don't care". Likewise, the right port interrupt flag ($\overline{INT}_R$) is asserted when the left port writes to memory location 3FF (HEX) and to clear the interrupt flag ($\overline{INT}_R$), the right port must access the memory location 3FF. The message (8 bits) at 3FE or 3FF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations 3FE and 3FF are not used as mail boxes, but as part of the random access memory. Refer to Table II for the interrupt operation.

BUSY LOGIC

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is “Busy”. The Busy pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of busy logic is not required or desirable for all applications. In some cases it may be useful to logically OR the busy outputs together and use any busy indication as an interrupt source to flag the event of an illegal or illogical operation. In slave mode the $\overline{BUSY}$ pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the $\overline{BUSY}$ pins High. If desired, unintended write operations can be prevented to a port by tying the Busy pin for that port Low.

The Busy outputs on the IDT7130 RAM (Master) are open drain type outputs and require open drain resistors to operate. If these RAMs are being expanded in depth, then the Busy indication for the resulting array does not require the use of an external AND gate.

WIDTH EXPANSION WITH BUSY LOGIC MASTER/SLAVE ARRAYS

When expanding an RAM array in width while using busy logic, one master part is used to decide which side of the RAM array will receive a busy indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the busy signal as a write inhibit signal. Thus on the IDT7130/IDT7140 RAMs the Busy pin is an output if the part is Master (IDT7130), and the Busy pin is an input if the part is a Slave (IDT7140) as shown in Figure 4.

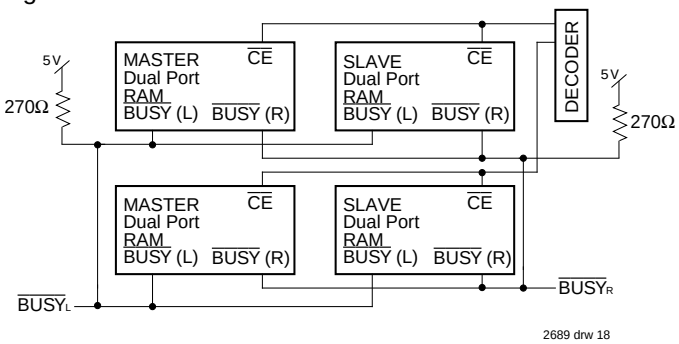
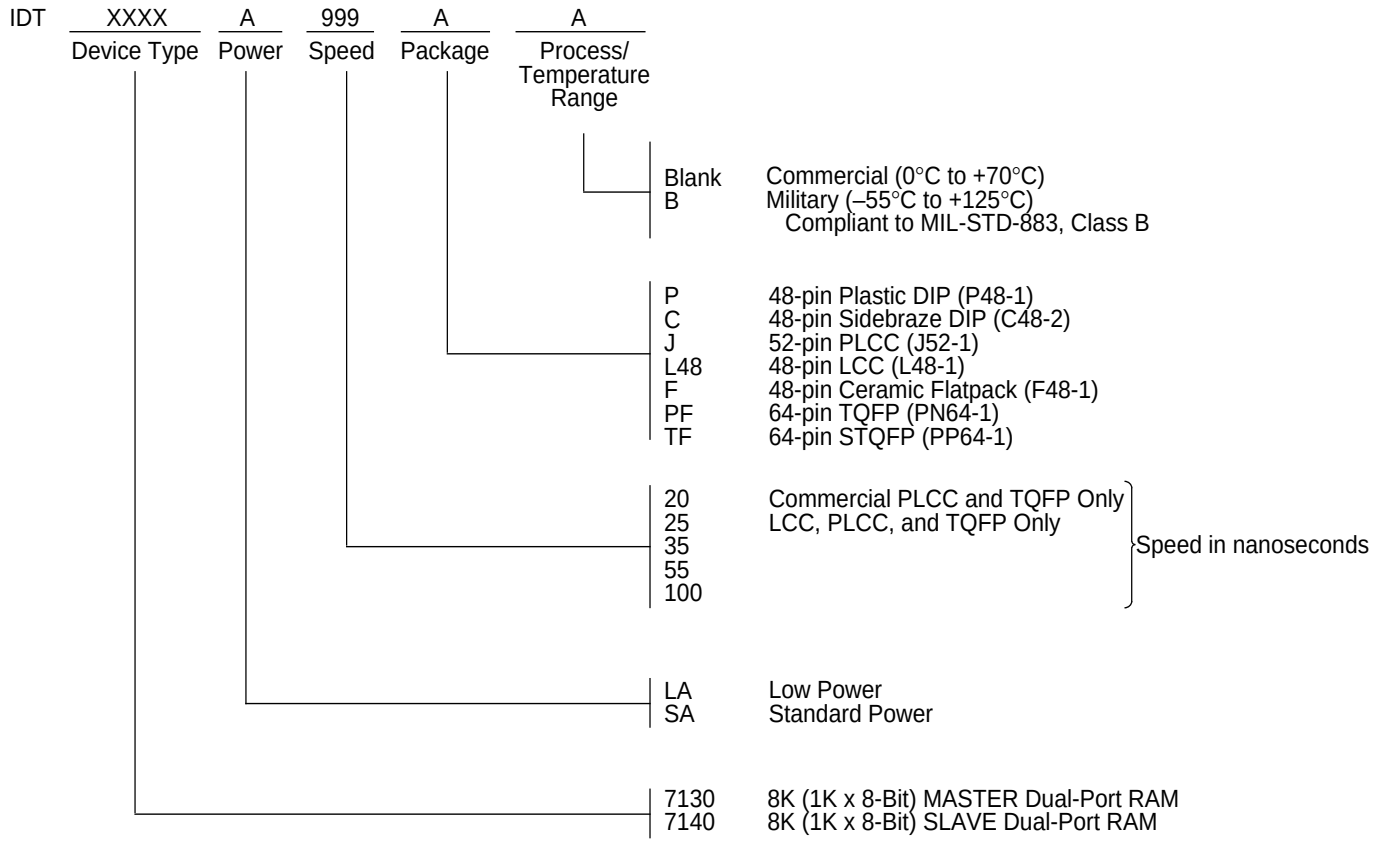


Figure 4. Busy and chip enable routing for both width and depth expansion with IDT7130 (Master) and IDT7140 (Slave) RAMs.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating busy on one side of the array and another master indicating busy on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The Busy arbitration, on a Master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a busy flag to be output from the master before the actual write pulse can be initiated with either the R/$\overline{W}$ signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

ORDERING INFORMATION



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